Wang Kang

List of Publications by Year
in descending order

152 papers	6,848 citations	76326 40 h-index	64796 79 g-index
153 all docs	153 docs citations	153 times ranked	3590 citing authors

#	Article	IF	Citations
1	Granularity-Driven Management for Reliable and Efficient Skyrmion Racetrack Memories. IEEE Transactions on Emerging Topics in Computing, 2023, 11, 95-111.	4.6	0
2	Surface acoustic wave controlled skyrmion-based synapse devices. Nanotechnology, 2022, 33, 115205.	2.6	9
3	A Novel Computing-in-Memory Platform Based on Hybrid Spintronic/CMOS Memory. IEEE Transactions on Electron Devices, 2022, 69, 1698-1705.	3.0	15
4	A Spintronic In-Memory Computing Network for Efficient Hamming Codec Implementation. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 2086-2090.	3.0	5
5	Novel Nonvolatile Lookup Table Design Based on Voltage-Controlled Spin Orbit Torque Memory. IEEE Transactions on Electron Devices, 2022, 69, 1677-1682.	3.0	1
6	Efficient and controllable magnetization switching induced by intermixing-enhanced bulk spinâ€“orbit torque in ferromagnetic multilayers. Applied Physics Reviews, 2022, 9, .	11.3	13
7	Foreword Special Issue on Spintronics-Devices and Circuits. IEEE Transactions on Electron Devices, 2022, 69, 1622-1628.	3.0	0
8	Linear Error Correction Codec Implementation Based on an In-Memory Computing Architecture for Nonvolatile Memories. IEEE Transactions on Electron Devices, 2022, 69, 3455-3461.	3.0	3
9	Anomalous Thermal-Assisted Spinâ€“Orbit Torque-Induced Magnetization Switching for Energy-Efficient Logic-in-Memory. ACS Nano, 2022, 16, 8264-8272.	14.6	9
10	A Mini Tutorial of Processing in Memory: From Principles, Devices to Prototypes. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 3044-3050.	3.0	3
11	Efficient Computation Reduction in Bayesian Neural Networks Through Feature Decomposition and Memorization. IEEE Transactions on Neural Networks and Learning Systems, 2021, 32, 1703-1712.	11.3	17
12	Design of an Area-Efficient Computing in Memory Platform Based on STT-MRAM. IEEE Transactions on Magnetics, 2021, 57, 1-4.	2.1	15
13	Magnetic skyrmions for unconventional computing. Materials Horizons, 2021, 8, 854-868.	12.2	74
14	A Survey of Test and Reliability Solutions for Magnetic Random Access Memories. Proceedings of the IEEE, 2021, 109, 149-169.	21.3	24
15	Toward Energy-Efficient STT-MRAM Design With Multi-Modes Reconfiguration. IEEE Transactions on Circuits and Systems II: Express Briefs, 2021, 68, 2633-2639.	3.0	9
16	Nonvolatile NULL Convention Logic Pipeline Using Magnetic Tunnel Junctions. IEEE Nanotechnology Magazine, 2021, 20, 703-707.	2.0	1
17	SpinLiM: Spin Orbit Torque Memory for Ternary Neural Networks Based on the Logic-in-Memory Architecture. , 2021, , .		6
18	3D Ferrimagnetic Device for Multi-Bit Storage and Efficient In-Memory Computing. IEEE Electron Device Letters, 2021, 42, 152-155.	3.9	8

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19	Experimental demonstration of voltage-gated spin-orbit torque switching in an antiferromagnet/ferromagnet structure. Physical Review B, 2021, 103, .	3.2	14
20	Exploiting Carbon Nanotube FET and Magnetic Tunneling Junction for Near-Memory-Computing Paradigm. IEEE Transactions on Electron Devices, 2021, 68, 1975-1979.	3.0	20
21	Ultrafast and Energy-Efficient Ferrimagnetic XNOR Logic Gates for Binary Neural Networks. IEEE Electron Device Letters, 2021, 42, 621-624.	3.9	6
22	Computing-in-Memory Paradigm Based on STT-MRAM with Synergetic Read/Write-Like Modes. , 2021, , .		2
23	HSC: A Hybrid Spin/CMOS Logic Based In-Memory Engine with Area-Efficient Mapping Strategy. , 2021, , .		0
24	Variability Study of Toggle Spin Torques Magnetic Random Access Memory. IEEE Transactions on Magnetics, 2021, 57, 1-5.	2.1	2
25	Spintronics for Energy- Efficient Computing: An Overview and Outlook. Proceedings of the IEEE, 2021, 109, 1398-1417.	21.3	112
26	Phase-change-assisted spin-transfer torque switching in perpendicular magnetic tunnel junctions. Applied Physics Letters, 2021, 119, .	3.3	22
27	Spintronic Computing-in-Memory Architecture Based on Voltage-Controlled Spinâ€“Orbit Torque Devices for Binary Neural Networks. IEEE Transactions on Electron Devices, 2021, 68, 4944-4950.	3.0	13
28	A Computing-in-memory Scheme with Series Bit-cell in STT-MRAM for Efficient Multi-bit Analog Multiplication. , 2021, , .		3
29	A Novel High Performance and Energy Efficient NUCA Architecture for STT-MRAM LLCs With Thermal Consideration. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2020, 39, 803-815.	2.7	7
30	SPINBIS: Spintronics-Based Bayesian Inference System With Stochastic Computing. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2020, 39, 789-802.	2.7	12
31	Amplitude and frequency modulation based on memristor-controlled spin nano-oscillators. Nanotechnology, 2020, 31, 045202.	2.6	2
32	Skyrmion-electronics: writing, deleting, reading and processing magnetic skyrmions toward spintronic applications. Journal of Physics Condensed Matter, 2020, 32, 143001.	1.8	268
33	A Self-Timed Voltage-Mode Sensing Scheme With Successive Sensing and Checking for STT-MRAM. IEEE Transactions on Circuits and Systems I: Regular Papers, 2020, 67, 1602-1614.	5.4	29
34	An STT-MRAM based reconfigurable computing-in-memory architecture for general purpose computing. CCF Transactions on High Performance Computing, 2020, 2, 272-281.	1.7	5
35	PRISM: Energy-Efficient Polymorphic Operation Based on Spin-Orbit Torque Memory for Reconfigurable Computing. , 2020, , .		1
36	Efficient Time-Domain In-Memory Computing Based on TST-MRAM. , 2020, , .		4

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37	Shift-Limited Sort: Optimizing Sorting Performance on Skyrmion Memory-Based Systems. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2020, 39, 4115-4128.	2.7	8
38	Perpendicular magnetization switching by large spinâ€“orbit torques from sputtered Bi₂Te₃*. Chinese Physics B, 2020, 29, 078505.	1.4	23
39	Stochastic Computing Implemented by Skyrmionic Logic Devices. Physical Review Applied, 2020, 13, .	3.8	39
40	Thermal Brownian Motion of Skyrmion for True Random Number Generation. IEEE Transactions on Electron Devices, 2020, 67, 2553-2558.	3.0	20
41	High-Density, Low-Power Voltage-Control Spin Orbit Torque Memory with Synchronous Two-Step Write and Symmetric Read Techniques. , 2020, , .		4
42	Erase-Hidden and Drivability-Improved Magnetic Non-Volatile Flip-Flops With NAND-SPIN Devices. IEEE Nanotechnology Magazine, 2020, 19, 446-454.	2.0	4
43	Skyrmion-based artificial synapses for neuromorphic computing. Nature Electronics, 2020, 3, 148-155.	26.0	346
44	Correlation of interfacial perpendicular magnetic anisotropy and interlayer exchange coupling in CoFe/W/CoFe structures. Journal Physics D: Applied Physics, 2020, 53, 334001.	2.8	3
45	A Novel In-memory Computing Scheme Based on Toggle Spin Torque MRAM. , 2020, , .		3
46	An In-memory Highly Reconfigurable Logic Circuit Based on Diode-assisted Enhanced Magnetoresistance Device. , 2020, , .		0
47	Hardware Security in Spin-based Computing-in-memory. ACM Journal on Emerging Technologies in Computing Systems, 2020, 16, 1-18.	2.3	5
48	Advanced Spin Orbit Torque Magnetic Random Access Memory with Field-Free Switching Schemes (Invited). , 2020, , .		3
49	Addressing Failure and Aging Degradation in MRAM/MeRAM-on-FDSOI Integration. IEEE Transactions on Circuits and Systems I: Regular Papers, 2019, 66, 239-250.	5.4	10
50	Magnetic Skyrmion Spectrum Under Voltage Excitation and its Linear Modulation. Physical Review Applied, 2019, 12, .	3.8	4
51	An Adaptive Thermal-Aware ECC Scheme for Reliable STT-MRAM LLC Design. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2019, 27, 1851-1860.	3.1	10
52	PXNOR-BNN: In/With Spin-Orbit Torque MRAM Preset-XNOR Operation-Based Binary Neural Networks. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2019, 27, 2668-2679.	3.1	41
53	Enhanced Spin-Orbit Torque and Multilevel Current-Induced Switching in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mrow><mml:mi mathvariant="normal">W</mml:mi></mml:mrow></mml:mrow><mml:mo>/</mml:mo><mml:mi>Co</mml:mi><mml:mtext>â”</mml:mtext></mml:m Heterostructure. Physical Review Applied, 2019, 12, .	3.8	39
54	Skyrmion-Based Ultra-Low Power Electric-Field-Controlled Reconfigurable (SUPER) Logic Gate. IEEE Electron Device Letters, 2019, 40, 1984-1987.	3.9	45

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55	Modulation of Heavy Metal/Ferromagnetic Metal Interface for Highâ€Performance Spintronic Devices. Advanced Electronic Materials, 2019, 5, 1900134.	5.1	64
56	Efficient Magnetic Domain Nucleation and Domain Wall Motion With Voltage Control Magnetic Anisotropy Effect and Antiferromagnetic/Ferromagnetic Coupling. IEEE Transactions on Magnetics, 2019, 55, 1-4.	2.1	5
57	CORN: In-Buffer Computing for Binary Neural Network. , 2019, , .		11
58	DASM: Data-Streaming-Based Computing in Nonvolatile Memory Architecture for Embedded System. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2019, 27, 2046-2059.	3.1	13
59	Compact Model for Negative Capacitance Enhanced Spintronics Devices. IEEE Transactions on Electron Devices, 2019, 66, 2795-2801.	3.0	4
60	Spintronic Processing Unit Within Voltage-Gated Spin Hall Effect MRAMs. IEEE Nanotechnology Magazine, 2019, 18, 473-483.	2.0	24
61	Skyrmion-Induced Memristive Magnetic Tunnel Junction for Ternary Neural Network. IEEE Journal of the Electron Devices Society, 2019, 7, 529-533.	2.1	13
62	Compact Modeling of Perpendicular-Magnetic-Anisotropy Double-Barrier Magnetic Tunnel Junction With Enhanced Thermal Stability Recording Structure. IEEE Transactions on Electron Devices, 2019, 66, 2431-2436.	3.0	51
63	Proposal of Toggle Spin Torques Magnetic RAM for Ultrafast Computing. IEEE Electron Device Letters, 2019, 40, 726-729.	3.9	74
64	Spintronic Processing Unit in Spin Transfer Torque Magnetic Random Access Memory. IEEE Transactions on Electron Devices, 2019, 66, 2017-2022.	3.0	50
65	Sky-RAM: Skyrmionic Random Access Memory. IEEE Electron Device Letters, 2019, 40, 722-725.	3.9	7
66	Novel Radiation Hardening Read/Write Circuits Using Feedback Connections for Spinâ€“Orbit Torque Magnetic Random Access Memory. IEEE Transactions on Circuits and Systems I: Regular Papers, 2019, 66, 1853-1862.	5.4	16
67	Ring-shaped content addressable memory based on spin orbit torque driven chiral domain wall motions. , 2019, , .		0
68	Spintronic Memories: From Memory to Computing-in-Memory. , 2019, , .		5
69	Ultra-Dense Ring-Shaped Racetrack Memory Cache Design. IEEE Transactions on Circuits and Systems I: Regular Papers, 2019, 66, 215-225.	5.4	31
70	Low-Power (1T1N) Skyrmionic Synapses for Spiking Neuromorphic Systems. IEEE Access, 2019, 7, 5034-5044.	4.2	18
71	An STT-MRAM Based in Memory Architecture for Low Power Integral Computing. IEEE Transactions on Computers, 2019, 68, 617-623.	3.4	10
72	Exploiting Spin-Orbit Torque Devices As Reconfigurable Logic for Circuit Obfuscation. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2019, 38, 57-69.	2.7	21

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73	A compact skyrmionic leakyâ€“integrateâ€“fire spiking neuron device. Nanoscale, 2018, 10, 6139-6146.	5.6	96
74	Negative Capacitance Enhanced All Spin Logic Devices With an Ultra-Low 1 mV Working Voltage. IEEE Journal of the Electron Devices Society, 2018, 6, 245-249.	2.1	9
75	High-Density NAND-Like Spin Transfer Torque Memory With Spin Orbit Torque Erase Operation. IEEE Electron Device Letters, 2018, 39, 343-346.	3.9	119
76	Addressing the Thermal Issues of STT-MRAM From Compact Modeling to Design Techniques. IEEE Nanotechnology Magazine, 2018, 17, 345-352.	2.0	33
77	A Fast and Power-Efficient Hardware Architecture for Visual Feature Detection in Affine-SIFT. IEEE Transactions on Circuits and Systems I: Regular Papers, 2018, 65, 3362-3375.	5.4	7
78	Skyrmions in Magnetic Tunnel Junctions. ACS Applied Materials & Interfaces, 2018, 10, 16887-16892.	8.0	68
79	Dynamics of a magnetic skyrmionium driven by spin waves. Applied Physics Letters, 2018, 112, .	3.3	43
80	Current-induced magnetization switching in atom-thick tungsten engineered perpendicular magnetic tunnel junctions with large tunnel magnetoresistance. Nature Communications, 2018, 9, 671.	12.8	259
81	Skyrmion Racetrack Memory With Random Information Update/Deletion/Insertion. IEEE Transactions on Electron Devices, 2018, 65, 87-95.	3.0	41
82	Demonstration of Multi-State Memory Device Combining Resistive and Magnetic Switching Behaviors. IEEE Electron Device Letters, 2018, 39, 684-687.	3.9	14
83	Self-Adaptive Write Circuit for Magnetic Tunneling Junction Memory With Voltage-Controlled Magnetic Anisotropy Effect. IEEE Nanotechnology Magazine, 2018, 17, 492-499.	2.0	15
84	A spin orbit torque based true random number generator with real-time optimization. , 2018, , .		6
85	Micromagnetic Simulation of Spin-Orbit Torque Induced Ultrafast Switching of In-Plane Magnetization. , 2018, , .		1
86	In-memory direct processing based on nanoscale perpendicular magnetic tunnel junctions. Nanoscale, 2018, 10, 21225-21230.	5.6	22
87	Field-free switching of a perpendicular magnetic tunnel junction through the interplay of spinâ€“orbit and spin-transfer torques. Nature Electronics, 2018, 1, 582-588.	26.0	304
88	Modeling and Evaluation of Sub-10-nm Shape Perpendicular Magnetic Anisotropy Magnetic Tunnel Junctions. IEEE Transactions on Electron Devices, 2018, 65, 5537-5544.	3.0	18
89	High-Density and Fast-Configuration Non-Volatile Look-Up Table Based on NAND-Like Spintronic Memory. , 2018, , .		4
90	A Full-Sensing-Margin Dual-Reference Sensing Scheme for Deeply-Scaled STT-RAM. IEEE Access, 2018, 6, 64250-64260.	4.2	6

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91	A Comparative Study on Racetrack Memories: Domain Wall vs. Skyrmion. , 2018, , .		10
92	Complementary Skyrmion Racetrack Memory Enables Voltage-Controlled Local Data Update Functionality. IEEE Transactions on Electron Devices, 2018, 65, 4667-4673.	3.0	7
93	Proposal for Multi-Gate Spin Field-Effect Transistor. IEEE Transactions on Magnetics, 2018, 54, 1-5.	2.1	4
94	Evaluation of Ultrahigh-Speed Magnetic Memories Using Field-Free Spinâ€“Orbit Torque. IEEE Transactions on Magnetics, 2018, 54, 1-5.	2.1	9
95	Enhancement of Perpendicular Magnetic Anisotropy Through Fe Insertion at the CoFe/W Interface. IEEE Transactions on Magnetics, 2018, 54, 1-5.	2.1	6
96	A Multilevel Cell STT-MRAM-Based Computing In-Memory Accelerator for Binary Convolutional Neural Network. IEEE Transactions on Magnetics, 2018, 54, 1-5.	2.1	51
97	Dynamics of Magnetic Skyrmion Clusters Driven by Spin-Polarized Current With a Spatially Varied Polarization. IEEE Magnetics Letters, 2018, 9, 1-5.	1.1	6
98	Progresses and challenges of spin orbit torque driven magnetization switching and application (Invited). , 2018, , .		15
99	Radiation-Hardening Techniques for Spin Orbit Torque-MRAM Peripheral Circuitry. IEEE Transactions on Magnetics, 2018, 54, 1-5.	2.1	11
100	Domain-Wall Motion Driven by Laplace Pressure in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>Co</mml:mi><mml:mtext>â^’</mml:mtext><mml:mi>Fe</mml:mi><mml:mtext>â^’</mml:mtext><mml:mi mathvariant="normal">B</mml:mi><mml:mo>/</mml:mo><mml:mi>MgO</mml:mi></mml:mrow></mml:math> Nanodots with Perpendicular Anisotropy. Physical Review Applied, 2018, 9, .	4.6	22
101	Magnetic skyrmion-based synaptic devices. Nanotechnology, 2017, 28, 08LT02.	2.6	223
102	Modeling and Exploration of the Voltage-Controlled Magnetic Anisotropy Effect for the Next-Generation Low-Power and High-Speed MRAM Applications. IEEE Nanotechnology Magazine, 2017, 16, 387-395.	2.0	112
103	Giant interfacial perpendicular magnetic anisotropy in MgO/CoFe/capping layer structures. Applied Physics Letters, 2017, 110, .	3.3	73
104	Compact Modeling and Evaluation of Magnetic Skyrmion-Based Racetrack Memory. IEEE Transactions on Electron Devices, 2017, 64, 1060-1068.	3.0	26
105	Interfacial Perpendicular Magnetic Anisotropy in Sub-20 nm Tunnel Junctions for Large-Capacity Spin-Transfer Torque Magnetic Random-Access Memory. IEEE Magnetics Letters, 2017, 8, 1-5.	1.1	25
106	Magnetic skyrmion-based artificial neuron device. Nanotechnology, 2017, 28, 31LT01.	2.6	169
107	A true random number generator based on parallel STT-MTJs. , 2017, , .		31
108	Influence of heavy metal materials on magnetic properties of Pt/Co/heavy metal tri-layered structures. Applied Physics Letters, 2017, 110, .	3.3	26

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109	A microwave field-driven transistor-like skyrmionic device with the microwave current-assisted skyrmion creation. Journal of Applied Physics, 2017, 122, .	2.5	24
110	Stateful Reconfigurable Logic via a Single-Voltage-Gated Spin Hall-Effect Driven Magnetic Tunnel Junction in a Spintronic Memory. IEEE Transactions on Electron Devices, 2017, 64, 4295-4301.	3.0	76
111	Partial spin absorption induced magnetization switching and its voltage-assisted improvement in an asymmetrical all spin logic device at the mesoscopic scale. Applied Physics Letters, 2017, 111, .	3.3	14
112	Skyrmion dynamics in width-varying nanotracks and implications for skyrmionic applications. Applied Physics Letters, 2017, 111, .	3.3	29
113	Large voltage-controlled magnetic anisotropy in the SrTiO3/Fe/Cu structure. Applied Physics Letters, 2017, 111, 152403.	3.3	16
114	Robust Ultra-Low Power Non-Volatile Logic-in-Memory Circuits in FD-SOI Technology. IEEE Transactions on Circuits and Systems I: Regular Papers, 2017, 64, 847-857.	5.4	85
115	PRESCOTT: Preset-based cross-point architecture for spin-orbit-torque magnetic random access memory. , 2017, , .		12
116	Novel Magnetic Tunneling Junction Memory Cell With Negative Capacitance-Amplified Voltage-Controlled Magnetic Anisotropy Effect. IEEE Transactions on Electron Devices, 2017, 64, 4919-4927.	3.0	6
117	Thermosiphon: A thermal aware NUCA architecture for write energy reduction of the STT-MRAM based LLCs. , 2017, , .		1
118	Compact modeling of high spin transfer torque efficiency double-barrier magnetic tunnel junction. , 2017, , .		4
119	Failure Analysis in Magnetic Tunnel Junction Nanopillar with Interfacial Perpendicular Magnetic Anisotropy. Materials, 2016, 9, 41.	2.9	72
120	Low Store Power, High Speed, High Density, Nonvolatile SRAM Design with Spin Hall Effect-Driven Magnetic Tunnel Junctions. IEEE Nanotechnology Magazine, 2016, , 1-1.	2.0	30
121	Large influence of capping layers on tunnel magnetoresistance in magnetic tunnel junctions. Applied Physics Letters, 2016, 109, .	3.3	26
122	Quantitative evaluation of reliability and performance for STT-MRAM. , 2016, , .		12
123	Voltage Controlled Magnetic Skyrmion Motion for Racetrack Memory. Scientific Reports, 2016, 6, 23164.	3.3	180
124	Skyrmion-Electronics: An Overview and Outlook. Proceedings of the IEEE, 2016, 104, 2040-2061.	21.3	289
125	Control and manipulation of a magnetic skyrmionium in nanostructures. Physical Review B, 2016, 94, .	3.2	137
126	Temperature Impact Analysis and Access Reliability Enhancement for 1T1MTJ STT-RAM. IEEE Transactions on Reliability, 2016, 65, 1755-1768.	4.6	40

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127	All Spin Artificial Neural Networks Based on Compound Spintronic Synapse and Neuron. IEEE Transactions on Biomedical Circuits and Systems, 2016, 10, 828-836.	4.0	84
128	Complementary Skyrmion Racetrack Memory With Voltage Manipulation. IEEE Electron Device Letters, 2016, 37, 924-927.	3.9	70
129	Reliability and performance evaluation for STT-MRAM under temperature variation. , 2016, , .		11
130	Compact Model of Dielectric Breakdown in Spin-Transfer Torque Magnetic Tunnel Junction. IEEE Transactions on Electron Devices, 2016, 63, 1762-1767.	3.0	132
131	Radiation-Induced Soft Error Analysis of STT-MRAM: A Device to Circuit Approach. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2016, 35, 380-393.	2.7	29
132	Origin of interfacial perpendicular magnetic anisotropy in MgO/CoFe/metallic capping layer structures. Scientific Reports, 2015, 5, 18173.	3.3	120
133	Magnetic nonâ€volatile flipâ€flop with spinâ€Hall assistance. Physica Status Solidi - Rapid Research Letters, 2015, 9, 375-378.	2.4	33
134	Perpendicular-anisotropy magnetic tunnel junction switched by spin-Hall-assisted spin-transfer torque. Journal Physics D: Applied Physics, 2015, 48, 065001.	2.8	176
135	Magnetic skyrmion transistor: skyrmion motion in a voltage-gated nanotrack. Scientific Reports, 2015, 5, 11369.	3.3	205
136	High-Frequency Low-Power Magnetic Full-Adder Based on Magnetic Tunnel Junction With Spin-Hall Assistance. IEEE Transactions on Magnetics, 2015, 51, 1-4.	2.1	28
137	Reconfigurable Codesign of STT-MRAM Under Process Variations in Deeply Scaled Technology. IEEE Transactions on Electron Devices, 2015, 62, 1769-1777.	3.0	135
138	Compact Model of Subvolume MTJ and Its Design Application at Nanoscale Technology Nodes. IEEE Transactions on Electron Devices, 2015, 62, 2048-2055.	3.0	78
139	Design Optimization and Analysis of Multicontext STT-MTJ/CMOS Logic Circuits. IEEE Nanotechnology Magazine, 2015, 14, 169-177.	2.0	29
140	Synchronous Non-Volatile Logic Gate Design Based on Resistive Switching Memories. IEEE Transactions on Circuits and Systems I: Regular Papers, 2014, 61, 443-454.	5.4	90
141	One-step majority-logic-decodable codes enable STT-MRAM for high speed working memories. , 2014, , .		3
142	Low Power Magnetic Full-Adder Based on Spin Transfer Torque MRAM. IEEE Transactions on Magnetics, 2013, 49, 4982-4987.	2.1	126
143	High reliability sensing circuit for deep submicron spin transfer torque magnetic random access memory. Electronics Letters, 2013, 49, 1283-1285.	1.0	49
144	ZFTL: A Zone-based Flash Translation Layer with a two-tier selective caching mechanism. , 2012, , .		2

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145	SER analysis and power allocation for hybrid cooperative transmission system. Journal of Systems Engineering and Electronics, 2012, 23, 661-670.	2.2	8
146	Ultra-High Density Content Addressable Memory Based on Current Induced Domain Wall Motion in Magnetic Track. IEEE Transactions on Magnetics, 2012, 48, 3219-3222.	2.1	41
147	Improving flash memory reliability with dynamic thresholds: Signal processing and coding schemes. , 2012, , .		2
148	Compact Modeling of Perpendicular-Anisotropy CoFeB/MgO Magnetic Tunnel Junctions. IEEE Transactions on Electron Devices, 2012, 59, 819-826.	3.0	330
149	A novel reader anti-collision protocol using Priority Cluster for dense reader RFID system. , 2011, , .		1
150	High Speed, High Stability and Low Power Sensing Amplifier for MTJ/CMOS Hybrid Logic Circuits. IEEE Transactions on Magnetics, 2009, 45, 3784-3787.	2.1	311
151	Dynamic compact model of Spin-Transfer Torque based Magnetic Tunnel Junction (MTJ). , 2009, , .		50
152	SpinCIM: spin orbit torque memory for ternary neural networks based on the computing-in-memory architecture. CCF Transactions on High Performance Computing, 0, , .	1.7	3